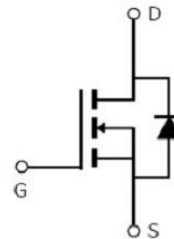


V_{DSS}	60V
$R_{DS(on)}$	7m (typ.)
I_D	58A



Advanced MOSFET process technology
 Special designed for PWM, load switching and
 general purpose applications
 Ultra low on-resistance with low gate charge
 Fast switching and reverse body recovery
 150 operating temperature



It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

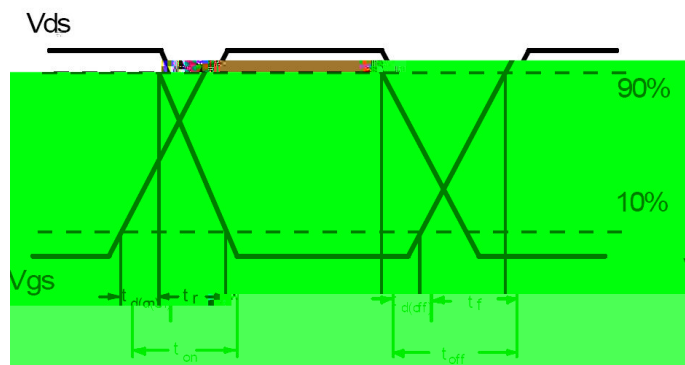
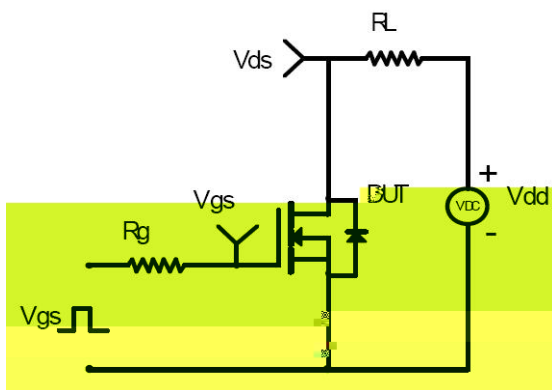
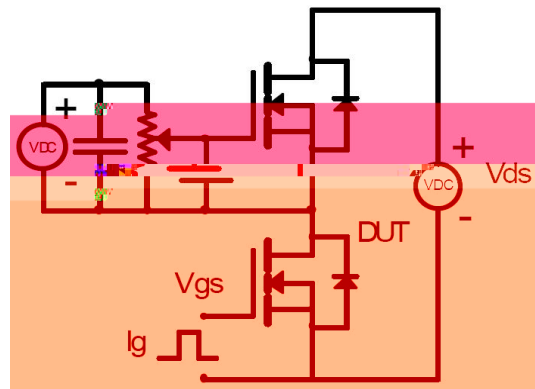
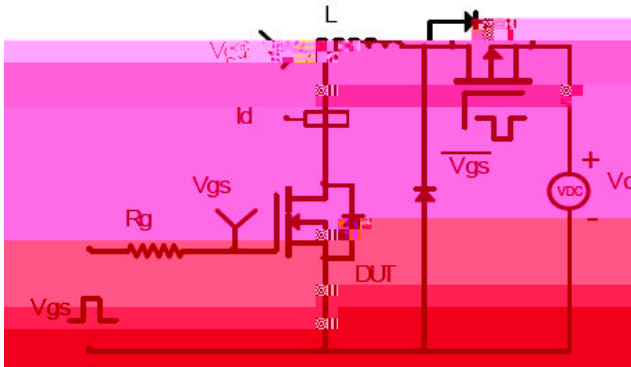
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	58	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	38	
I_{DM}	Pulsed Drain Current	232	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	58	W
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$



R _{JC}	Junction-to-case	—	2.14	/W

@T_J=25 unless otherwise specified

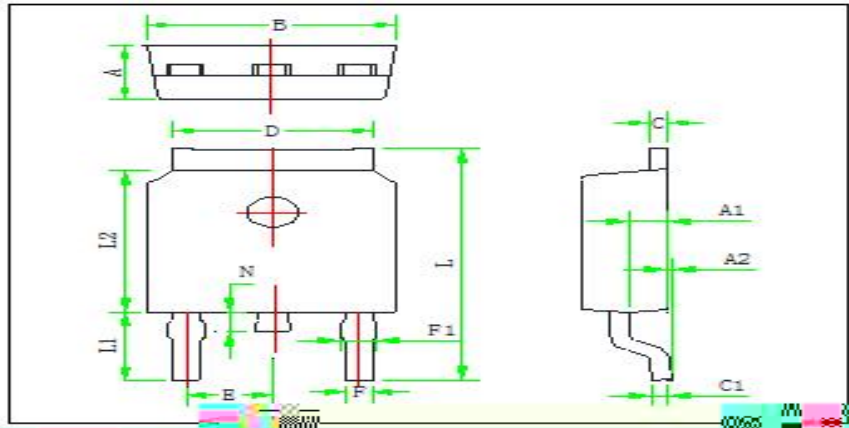
V _{(BR)DSS}	Drain-to-Source breakdown voltage	60	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	7	9.1	m	V _{GS} =10V, I _D = 20A
		—	8.5	11.1	m	V _{GS} =4.5V, I _D = 10A
V _{GS(th)}	Gate threshold voltage	1	—	2.5	V	V _{DS} = V _{GS} , I _D = 250μA
I _{DSS}	Drain-to-Source leakage current	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
I _{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V _{GS} = 20V
		—	—	±		



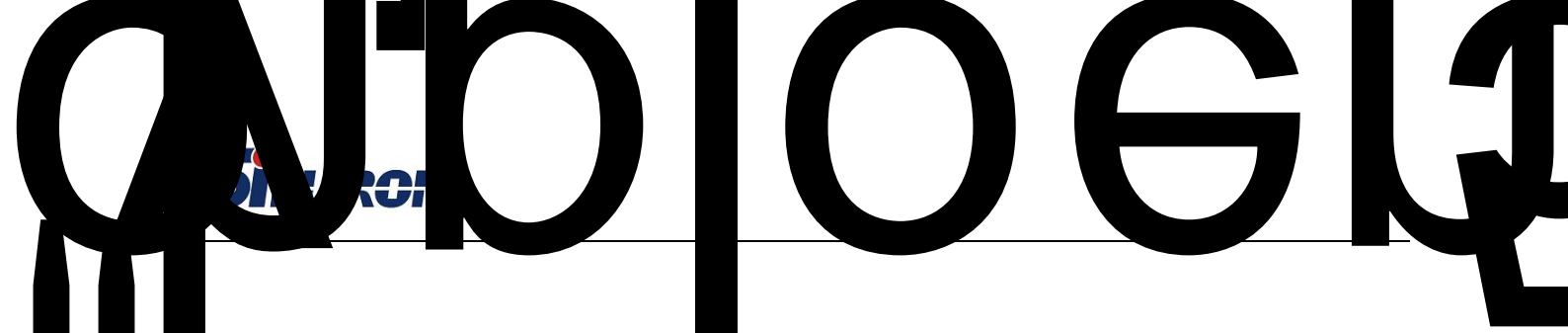
Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.



Symbol	Min	Typ	Max
A	2.20	2.30	2.40
A1	0.91	1.01	1.11
A2	0.05	0.15	0.25
B	6.45	6.60	6.75
C	0.45	0.50	0.58
C1	0.45	0.50	0.58
D	5.12	5.32	5.52
E		2.286 TYP	
F	0.66	0.76	0.86
F1	0.66	0.86	1.06
L	9.60	9.90	10.20
L1	2.6	2.8	3.0
L2	5.95	6.10	6.25
N	0.60	0.80	1.00



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